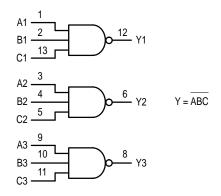
Triple 3-Input NAND Gate

High-Performance Silicon-Gate CMOS

The MC74HC10 is identical in pinout to the LS10. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

- Output Drive Capability: 10 LSTTL Loads
- · Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard
- Chip Complexity: 36 FETs or 9 Equivalent Gates

LOGIC DIAGRAM



PIN 14 = V_{CC} PIN 7 = GND

MC74HC10



N SUFFIX

PLASTIC PACKAGE CASE 646-06



D SUFFIX

SOIC PACKAGE CASE 751A-03

ORDERING INFORMATION

MC74HCXXN Plastic MC74HCXXD SOIC

PIN ASSIGNMENT

| A1 [| 1 • | | □ v _{cc} |
|-------|-----|----|-------------------|
| B1 [| 2 | 13 |] C1 |
| A2 [| 3 | 12 |] Y1 |
| B2 [| 4 | 11 |] C3 |
| C2 [| 5 | 10 |] B3 |
| Y2 [| 6 | 9 |] A3 |
| GND [| 7 | 8 |] Y3 |
| | | | |

FUNCTION TABLE

| | Inputs | | Output |
|---|--------|---|--------|
| Α | В | С | Υ |
| L | Х | Х | Н |
| Х | L | X | H |
| Х | Χ | L | H |
| Н | Н | Н | L |

MAXIMUM RATINGS*

| Symbol | Parameter | Value | Unit |
|------------------|--|--------------------------------|------|
| VCC | DC Supply Voltage (Referenced to GND) | - 0.5 to + 7.0 | V |
| V _{in} | DC Input Voltage (Referenced to GND) | - 1.5 to V _{CC} + 1.5 | V |
| V _{out} | DC Output Voltage (Referenced to GND) | -0.5 to V _{CC} + 0.5 | V |
| l _{in} | DC Input Current, per Pin | ± 20 | mA |
| l _{out} | DC Output Current, per Pin | ± 25 | mA |
| ICC | DC Supply Current, V _{CC} and GND Pins | ± 50 | mA |
| PD | Power Dissipation in Still Air Plastic DIP† SOIC Package† | 750 500 | mW |
| T _{stg} | Storage Temperature | - 65 to + 150 | °C |
| TL | Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package) | 260 | °C |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq VCC. Unused inputs must always be tied to an appropriate logic voltage

level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: -7 mW/°C from 65° to 125° C

For high frequency or heavy load considerations, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit | |
|------------------------------------|--|---|-------------|--------------------|----|
| VCC | DC Supply Voltage (Referenced to GND) | | | 6.0 | ٧ |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage (Referenced to GND) | | | Vcc | V |
| TA | Operating Temperature, All Package Types | | | + 125 | °C |
| t _r , t _f | Input Rise and Fall Time (Figure 1) | / _{CC} = 2.0 V / _{CC} = 4.5 V / _{CC} = 6.0 V | 0 0 0 | 1000 500 400 | ns |

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| | | | | Guaranteed Limit | | | |
|-----------------|---|--|-------------------|--------------------|--------------------|--------------------|------|
| Symbol | Parameter | Test Conditions | V _{CC} | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| VIH | Minimum High–Level Input Voltage | $V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$ | 2.0 4.5 6.0 | 1.5 3.15 4.2 | 1.5 3.15 4.2 | 1.5 3.15 4.2 | V |
| VIL | Maximum Low–Level Input Voltage | $V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$ | 2.0 4.5 6.0 | 0.3 0.9 1.2 | 0.3 0.9 1.2 | 0.3 0.9 1.2 | V |
| VOH | Minimum High–Level Output Voltage | $V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 4.5 6.0 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | V |
| | | $V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} I_{\text{out}} \le 4.0 \text{ mA} $ $ I_{\text{out}} \le 5.2 \text{ mA}$ | 4.5 6.0 | 3.98 5.48 | 3.84 5.34 | 3.70 5.20 | |
| VOL | Maximum Low–Level Output Voltage | $V_{in} = V_{IH}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 4.5 6.0 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | V |
| | | $V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} I_{\text{out}} \le 4.0 \text{ mA} I_{\text{out}} \le 5.2 \text{ mA}$ | 4.5 6.0 | 0.26 0.26 | 0.33 0.33 | 0.40 0.40 | |
| l _{in} | Maximum Input Leakage Current | $V_{in} = V_{CC}$ or GND | 6.0 | ± 0.1 | ± 1.0 | ± 1.0 | μΑ |
| lcc | Maximum Quiescent Supply Current (per Package) | V _{in} = V _{CC} or GND I _{out} = 0 µA | 6.0 | 2 | 20 | 40 | μА |

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

MOTOROLA 2

^{*} Maximum Ratings are those values beyond which damage to the device may occur.

 $[\]label{prop:conditions} Functional\ operation\ should\ be\ restricted\ to\ the\ Recommended\ Operating\ Conditions.$

[†]Derating — Plastic DIP: – 10 mW/ $^{\circ}$ C from 65 $^{\circ}$ to 125 $^{\circ}$ C

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

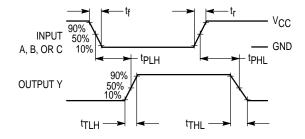
| | | | Guaranteed Limit | | | |
|--|---|-------------------|------------------|-----------------|-----------------|------|
| Symbol | Parameter | V _{CC} | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Input A, B, or C to Output Y (Figures 1 and 2) | 2.0 4.5 6.0 | 95 19 16 | 120 24 20 | 145 29 25 | ns |
| tTLH, tTHL | Maximum Output Transition Time, Any Output (Figures 1 and 2) | 2.0 4.5 6.0 | 75 15 13 | 95 19 16 | 110 22 19 | ns |
| C _{in} | Maximum Input Capacitance | _ | 10 | 10 | 10 | pF |

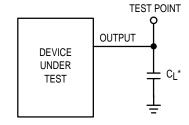
NOTES:

- 1. For propagation delays with loads other than 50 pF, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).
- 2. Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

| | | Typical @ 25°C, V _{CC} = 5.0 V | |
|----|---|---|----|
| CP | Power Dissipation Capacitance (Per Gate)* | 25 | pF |

^{*} Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).



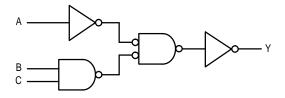


* Includes all probe and jig capacitance

Figure 1. Switching Waveforms

Figure 2. Test Circuit

EXPANDED LOGIC DIAGRAM (1/3 OF THE DEVICE)



MOTOROLA

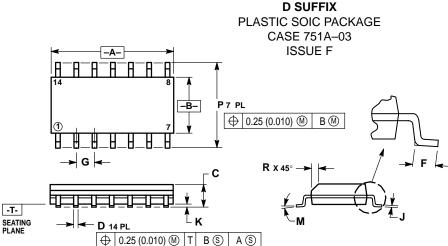
OUTLINE DIMENSIONS

N SUFFIX PLASTIC DIP PACKAGE CASE 646-06 ISSUE L ISSUE L

NOTES:

- LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE
 POSITION AT SEATING PLANE AT MAXIMUM
 MATERIAL CONDITION
- DIMENSION L TO CENTER OF LEADS WHEN
 FORMED PARALLEI
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.
- 4. ROUNDED CORNERS OPTIONAL.

| | INCHES | | MILLIN | IETERS | |
|-----|-----------|-------|--------|--------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 0.715 | 0.770 | 18.16 | 19.56 | |
| В | 0.240 | 0.260 | 6.10 | 6.60 | |
| С | 0.145 | 0.185 | 3.69 | 4.69 | |
| D | 0.015 | 0.021 | 0.38 | 0.53 | |
| F | 0.040 | 0.070 | 1.02 | 1.78 | |
| G | 0.100 | BSC | 2.54 | BSC | |
| Н | 0.052 | 0.095 | 1.32 | 2.41 | |
| J | 0.008 | 0.015 | 0.20 | 0.38 | |
| K | 0.115 | 0.135 | 2.92 | 3.43 | |
| L | 0.300 BSC | | 7.62 | BSC | |
| M | 0° | 10° | 0° | 10° | |
| N | 0.015 | 0.039 | 0.39 | 1.01 | |



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M. 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIM | IETERS | INC | HES |
|-----|--------|--------|------------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 8.55 | 8.75 | 0.337 | 0.344 |
| В | 3.80 | 4.00 | 0.150 | 0.157 |
| С | 1.35 | 1.75 | 0.054 | 0.068 |
| D | 0.35 | 0.49 | 0.014 | 0.019 |
| F | 0.40 | 1.25 | 0.016 | 0.049 |
| G | 1.27 | BSC | 0.050 | BSC |
| J | 0.19 | 0.25 | 0.008 | 0.009 |
| K | 0.10 | 0.25 | 0.004 | 0.009 |
| M | 0° | 7° | 0° | 7° |
| Р | 5.80 | 6.20 | 0.228 0.24 | |
| R | 0.25 | 0.50 | 0.010 | 0.019 |

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MC74HC10/D